

EDJ120S20R1L

ev™ Silicon Carbide Schottky Diode 1200V, 20A

Features

- Zero Reverse Recovery Current
- Low Forward Voltage
- High Surge Current Capability
- Independent of Temperature Switching Behavior
- Positive Temperature Coefficient
- Max Junction Temperature 175 °C
- Pb-free, Halogen Free, and RoHS Compliant

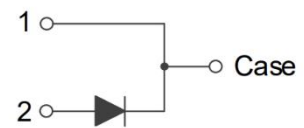
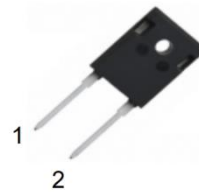
Benefits

- Higher Efficiency
- Ease of Paralleling
- Increased Power Density
- Reduced Cooling Requirements

Applications

- Solar Inverters
- Power Factor Correction
- Industrial Power Supply
- EV Charging Station

| V_{RRM} | $I_F, T_C=25^\circ C$ | $T_{J, Max}$ | Q_C, Typ |
|-----------|-----------------------|--------------|------------|
| 1200V | 20A | 175°C | 120nC |



Ordering Information

| Part Number | Package | Shipping | Quantity |
|--------------|-----------|----------|----------|
| EDJ120S20R1L | TO-247-2L | Tube | 30 units |

Absolute Maximum Ratings ($T_C=25^\circ C$, unless otherwise specified)

| Symbol | Parameter | Value | Unit |
|----------------|---|--------------------------------|------|
| V_{RRM} | Repetitive Peak Reverse Voltage | 1200 | V |
| I_F | Forward Current | $T_C=150^\circ C$ 20 | A |
| $I_{F,SM}$ | Non-Repetitive Forward Surge Current | $T_C=25^\circ C, t_p=10ms$ | 140 |
| | | $T_C=150^\circ C, t_p=10ms$ | 120 |
| $I_{F,Max}$ | Non-Repetitive Peak Forward Current | $T_C=25^\circ C, t_p=10\mu s$ | 1200 |
| | | $T_C=150^\circ C, t_p=10\mu s$ | 1000 |
| I^2dt value | $\int I^2 dt$ | $T_C=25^\circ C, t_p=10ms$ | 98 |
| | | $T_C=150^\circ C, t_p=10ms$ | 72 |
| P_{tot} | Power Dissipation | $T_C=25^\circ C$ 289 | W |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to 175 | °C |

■ Thermal Characteristics

| Symbol | Parameter | Value | Unit |
|-----------------|--|-------|------|
| $R_{\theta JC}$ | Maximum Thermal Resistance, Junction to Case | 0.52 | °C/W |

■ Electrical Characteristics (T_C=25°C, unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|---------------------------|------------------------------|------|------|------|---------|
| V_F | Forward Voltage | $I_F=20A, T_J=25^\circ C$ | | 1.45 | 1.75 | V |
| | | $I_F=20A, T_J=175^\circ C$ | | 1.95 | | |
| I_R | Reverse Current | $V_R=1200V, T_C=25^\circ C$ | | | 100 | μA |
| | | $V_R=1200V, T_J=175^\circ C$ | | | 300 | |
| Q_C | Total Capacitive Charge | $V_R=800V, T_J=25^\circ C$ | | 120 | | nC |
| C | Total Capacitance | $V_R=1V, f=1MHz$ | | 1360 | | pF |
| | | $V_R=800V, f=1MHz$ | | 85 | | |
| E_C | Capacitance Stored Energy | $V_R=800V$ | | 35 | | μJ |

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